

PMP41037_GaN REV E1 Bill of Materials

Designator	Quantity	Value	PartNumber	Manufacturer	Description	PackageReference
C1, C3	2	10uF	GRM21BZ71E106KE15L	MuRata	CAP, CERM, 10 uF, 25 V, +/- 10%, X7R, 0805	805
C2, C4	2	100pF	8.85012E+11	Würth Elektronik	CAP, CERM, 100 pF, 50 V, +/- 10%, X7R, 0402	402
C5, C6, C7, C8	4	0.022uF	C1206C223KDRACTU	Kemet	CAP, CERM, 0.022 µF, 1000 V, +/- 10%, X7R, AEC-Q200 Grade 1, 1206	1206
HS1, HS2	2			Texas Instruments	Copper Heatsink 8*11mm	
R1, R2	2	120k	RG1608N-124-W-T1	Susumu Co Ltd	RES, 120 k, 0.05%, 0.1 W, AEC-Q200 Grade 0, 0603	603
R3	1	100	CRCW0402300RJNED	Vishay-Dale	RES, 300, 5%, 0.063 W, AEC-Q200 Grade 0, 0402	402
R4	1	300	CRCW0402300RJNED	Vishay-Dale	RES, 300, 5%, 0.063 W, AEC-Q200 Grade 0, 0402	402
R5, R6	2	0	RCS06030000Z0EA	Vishay-Dale	RES, 0, 0%, 0.25 W, AEC-Q200 Grade 0, 0603	603
U7, U8	2		LMG3622REQ	Texas Instruments	650-V GaN FET With Integrated Driver and Current Sense Emulation	VQFN38